

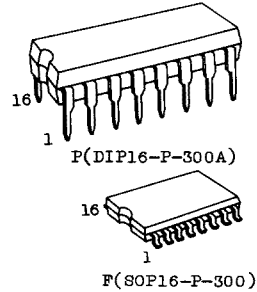
TC4572BP/BF

C²MOS DIGITAL INTEGRATED CIRCUIT
SILICON MONOLITHIC

TC4572BP/TC4572BF HEX GATE
(4 INVERTERS Plus 2-Input NOR Gate Plus 2-Input NAND Gate)

TC4572BP/BF is a multiple gate that contains 4-circuit inverters, 1 circuit 2-input NOR GATE, and 1 circuit 2-input NAND GATE in one package.

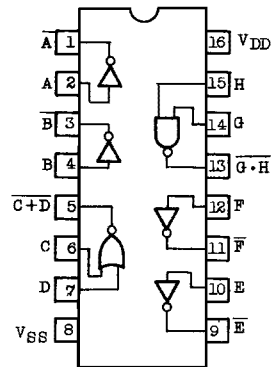
Since each gate is of "B" type equipped with a buffer consisting of 2-stage inverters, it has high noise immunity.



ABSOLUTE MAXIMUM RATINGS

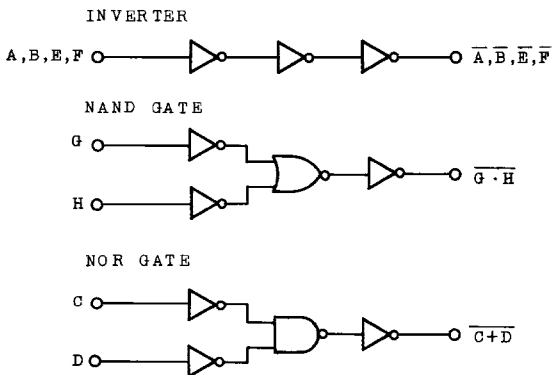
CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V _{DD}	V _{SS} - 0.5 ~ V _{SS} + 20	V
Input Voltage	V _{IN}	V _{SS} - 0.5 ~ V _{DD} + 0.5	V
Output Voltage	V _{OUT}	V _{SS} - 0.5 ~ V _{DD} + 0.5	V
DC Input Current	I _{IN}	±10	mA
Power Dissipation	P _D	300 (DIP)/180 (SOIC)	mW
Operating Temperature Range	T _A	-40 ~ 85	°C
Storage Temperature Range	T _{stg}	-65 ~ 150	°C
Lead Temp./Time	T _{sol}	260°C · 10 sec	

PIN ASSIGNMENT



(TOP VIEW)

LOGIC DIAGRAM



Weight

DIP16-P-300A : 1.0g (Typ.)

SOP16-P-300 : 0.16g (Typ.)

RECOMMENDED OPERATING CONDITIONS (V_{SS}=0V)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DC Supply Voltage	V _{DD}	3	-	18	V
Input Voltage	V _{IN}	0	-	V _{DD}	V

STATIC ELECTRICAL CHARACTERISTICS (V_{SS}=0V)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	V _{DD} (V)	-40°C		25°C			85°C		UNITS	
				MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.		
High-Level Output Voltage	V _{OH}	I _{OUT} < 1μA V _{IN} =V _{SS} , V _{DD}	5	4.95	-	4.95	5.00	-	4.95	-	V	
			10	9.95	-	9.95	10.00	-	9.95	-		
			15	14.95	-	14.95	15.00	-	14.95	-		
Low-Level Output Voltage	V _{OL}	I _{OUT} < 1μA V _{IN} =V _{SS} , V _{DD}	5	-	0.05	-	0.00	0.05	-	0.05	V	
			10	-	0.05	-	0.00	0.05	-	0.05		
			15	-	0.05	-	0.00	0.05	-	0.05		
Output High Current	I _{OH}	V _{OH} =4.6V V _{OH} =2.5V V _{OH} =9.5V V _{OH} =13.5V V _{IN} =V _{SS} , V _{DD}	5	-0.61	-	-0.51	-1.0	-	-0.42	-	mA	
			5	-2.5	-	-2.1	-4.0	-	-1.7	-		
			10	-1.5	-	-1.3	-2.2	-	-1.1	-		
			15	-4.0	-	-3.4	-9.0	-	-2.8	-		
Output Low Current	I _{OL}	V _{OL} =0.4V V _{OL} =0.5V V _{OL} =1.5V V _{IN} =V _{SS} , V _{DD}	5	0.61	-	0.51	1.5	-	0.42	-	mA	
			10	1.5	-	1.3	3.8	-	1.1	-		
			15	4.0	-	3.4	15.0	-	2.8	-		
			15	4.0	-	3.4	15.0	-	2.8	-		
Input High Voltage	V _{IH}	V _{OUT} =0.5V, 4.5V V _{OUT} =1.0V, 9.0V V _{OUT} =1.5V, 13.5V I _{OUT} < 1μA	5	3.5	-	3.5	2.75	-	3.5	-	V	
			10	7.0	-	7.0	5.5	-	7.0	-		
			15	11.0	-	11.0	8.25	-	11.0	-		
			15	11.0	-	11.0	8.25	-	11.0	-		
Input Low Voltage	V _{IL}	V _{OUT} =0.5V, 4.5V V _{OUT} =1.0V, 9.0V V _{OUT} =1.5V, 13.5V I _{OUT} < 1μA	5	-	1.5	-	2.25	1.5	-	1.5	V	
			10	-	3.0	-	4.5	3.0	-	3.0		
			15	-	4.0	-	6.75	4.0	-	4.0		
			15	-	4.0	-	6.75	4.0	-	4.0		
Input Current	"H" Level	I _{IH}	V _{IH} =18V	18	-	0.1	-	10 ⁻⁵	0.1	-	1.0	μA
	"L" Level	I _{IL}	V _{IL} =0V	18	-	-0.1	-	-10 ⁻⁵	-0.1	-	-1.0	
Quiescent Device Current	I _{DD}	V _{IN} =V _{SS} , V _{DD} *	5	-	0.25	-	0.001	0.25	-	3.8	μA	
			10	-	0.5	-	0.001	0.5	-	7.5		
			15	-	1.0	-	0.002	1.0	-	15		

* All valid input combinations.

TC4572BP/BF

DYNAMIC ELECTRICAL CHARACTERISTICS (Ta=25°C, VSS=0V, CL=50pF)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{DD} (V)	MIN.	TYP.	MAX.	UNITS
			5				
Output Transition Time (Low to High)	t_{TLH}		5	-	80	200	ns
			10	-	50	100	
			15	-	40	80	
Output Transition Time (High to Low)	t_{THL}		5	-	80	200	
			10	-	50	100	
			15	-	40	80	
Propagation Delay Time (INVERTER)	t_{pLH} t_{pHL}		5	-	90	200	
			10	-	40	110	
			15	-	30	85	
Propagation Delay Time (NAND)	t_{pLH} t_{pHL}		5	-	95	200	
			10	-	45	110	
			15	-	35	85	
Propagation Delay Time (NOR)	t_{pLH} t_{pHL}		5	-	95	200	
			10	-	45	110	
			15	-	35	85	
Input Capacitance	C _{IN}			-	5	7.5	pF

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

